

isc Silicon PNP Power Transistor

KTA1659

DESCRIPTION

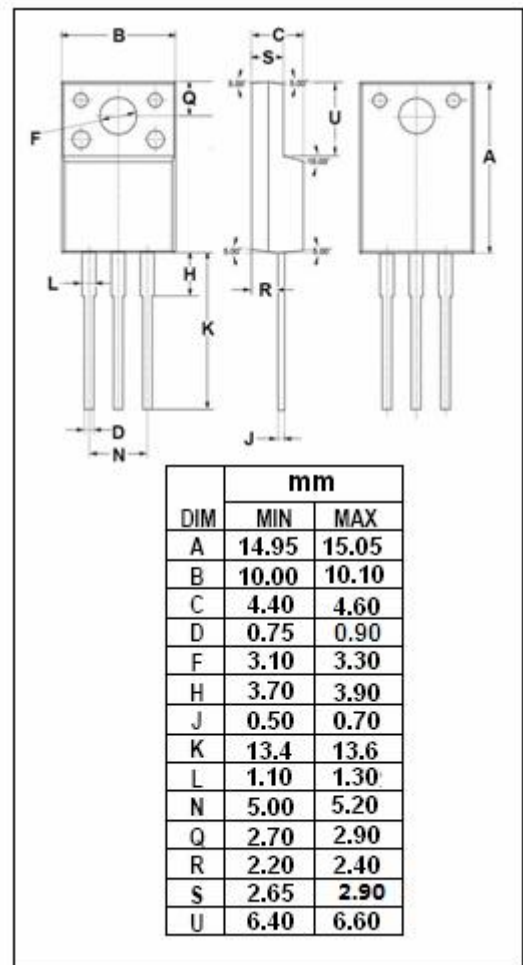
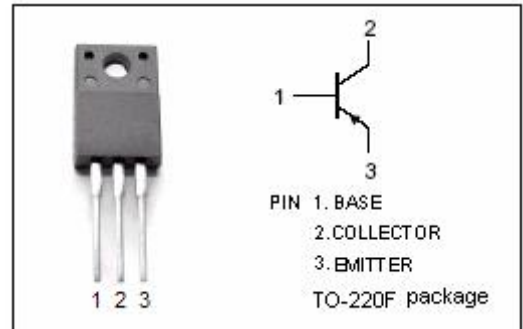
- High Collector-Emitter Breakdown Voltage
 $V_{CEO} = -160V(\text{Min})$
- Complement to Type KTC4370

APPLICATIONS

- Designed for high voltage applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
$I_{C(DC)}$	Collector Current(DC)	-1.5	A
$I_{B(DC)}$	Base Current	-0.15	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	20	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor**KTA1659****ELECTRICAL CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA; I _B = 0	-160			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -500mA; I _B = -50mA			-1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -500mA; V _{CE} = -5V			-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -160V; I _E = 0			-1.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-1.0	μ A
h _{FE}	DC Current Gain	I _C = -100mA; V _{CE} = -5V	70		240	
C _{OB}	Output Capacitance	I _E =0; V _{CB} = -10V; f= 1.0MHz		30		pF
f _T	Current-Gain—Bandwidth Product	I _C =-100mA; V _{CE} = -10V		100		MHz

◆ h_{FE} Classifications

O	Y
70-140	120-240